

MA3X158

Silicon epitaxial planar type

For small power rectification and surge absorption

■ Features

- High reverse voltage V_R
- Large forward current $I_{F(AV)}$
- Small package and allowing automatic mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

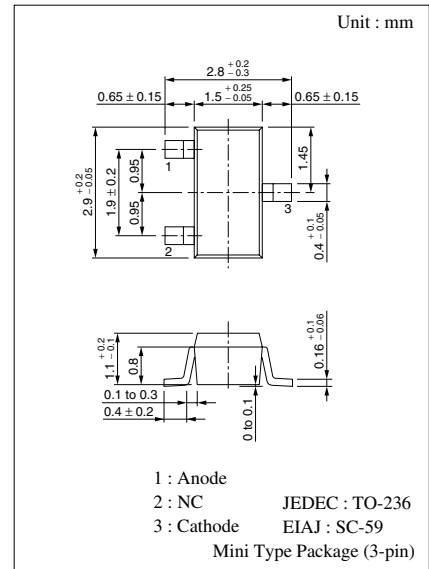
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Repetitive peak reverse voltage	V_{RRM}	250	V
Non-repetitive peak forward surge voltage	V_{RSM}	300	V
Output current	$I_{F(AV)}$	100	mA
Non-repetitive peak forward surge current*	I_{FSM}	500	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200 \text{ V}$			1.0	μA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.3	V

Note) Rated input/output frequency: 3 MHz



Marking Symbol: M1C

Internal Connection

